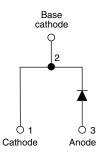
**Vishay Semiconductors** 

### HEXFRED<sup>®</sup> Ultrafast Soft Recovery Diode, 8 A



www.vishay.com



PRIMARY CHARACTERISTICS				
I <sub>F(AV)</sub>	8 A			
V <sub>R</sub>	1200 V			
V <sub>F</sub> at I <sub>F</sub>	2.4 V			
t <sub>rr</sub> typ.	28 ns			
T <sub>J</sub> max.	150 °C			
Package	TO-247AC 2L			
Circuit configuration	Single			

#### FEATURES

- Ultrafast and ultrasoft recovery
- Very low  $I_{RRM}$  and  $Q_{rr}$
- Designed and qualified according to JEDEC<sup>®</sup>-JESD 47
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

#### BENEFITS

- Reduced RFI and EMI
- Reduced power loss in diode and switching transistor
- Higher frequency operation
- Reduced snubbing
- Reduced parts count

#### DESCRIPTION

VS-HFA08PB120... is a state of the art ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 1200 V and 8 A continuous current, the VS-HFA08PB120... is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (I<sub>BBM</sub>) and does not exhibit any tendency to "snap-off" during the t<sub>b</sub> portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED VS-HFA08PB120... is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Cathode to anode voltage	V <sub>R</sub>		1200	V		
Maximum continuous forward current	I <sub>F</sub>	T <sub>C</sub> = 100 °C	8			
Single pulse forward current	I <sub>FSM</sub>	t <sub>p</sub> = 10 ms	130	А		
Maximum repetitive forward current	I <sub>FRM</sub>		32			
Maximum neuror discipation	P <sub>D</sub>	T <sub>C</sub> = 25 °C	73.5	W		
Maximum power dissipation		T <sub>C</sub> = 100 °C	29	vv		
Operating junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-55 to +150	°C		

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<b>ELECTRICAL SPECIFICATIONS</b> (T <sub>J</sub> = 25 $^{\circ}$ C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
Cathode to anode breakdown voltage	V <sub>BR</sub>	I <sub>R</sub> = 100 μA		1200	-	-	
		I <sub>F</sub> = 8.0 A		-	2.6	3.3	V
Maximum forward voltage V <sub>F</sub>	$V_{FM}$	I <sub>F</sub> = 16 A	See fig. 1	-	3.4	4.3	
		I <sub>F</sub> = 8.0 A, T <sub>J</sub> = 125 °C		-	2.4	3.1	
Maximum reverse		$V_{R} = V_{R}$ rated	Coofin 0	-	0.31	10	μA
leakage current	IRM	$T_J$ = 125 °C, $V_R$ = 0.8 x $V_R$ rated	See fig. 2	-	135	1000	
Junction capacitance	CT	V <sub>R</sub> = 200 V See fig. 3		-	11	20	pF
Series inductance	L <sub>S</sub>	Measured lead to lead 5 mm from p	ackage body	-	8.0	-	nH

DYNAMIC RECOVERY CHARACTERISTICS (T <sub>J</sub> = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS
<b>.</b>	t <sub>rr</sub>	$I_F = 1.0 \text{ A}, \text{ d}I_F/\text{d}t = 200$	$I_F = 1.0 \text{ A}, \text{ d}I_F/\text{d}t = 200 \text{ A}/\mu\text{s}, \text{ V}_R = 30 \text{ V}$		28	-	
Reverse recovery time See fig. 5, 10	t <sub>rr1</sub>	T <sub>J</sub> = 25 °C		-	63	95	ns
	t <sub>rr2</sub>	T <sub>J</sub> = 125 °C	I <sub>F</sub> = 8.0 A dI <sub>F</sub> /dt = 200 A/μs V <sub>R</sub> = 200 V	-	106	160	
Peak recovery current See fig. 6	I <sub>RRM1</sub>	T <sub>J</sub> = 25 °C		-	4.5	8.0	- A
	I <sub>RRM2</sub>	T <sub>J</sub> = 125 °C		-	6.2	11	
Reverse recovery charge	Q <sub>rr1</sub>	T <sub>J</sub> = 25 °C		-	140	380	
See fig. 7	Q <sub>rr2</sub>	T <sub>J</sub> = 125 °C		-	335	880	nC
Peak rate of recovery	dl <sub>(rec)M</sub> /dt1	T <sub>J</sub> = 25 °C		-	133	-	
current during t <sub>b</sub> See fig. 8	dl <sub>(rec)M</sub> /dt2	T <sub>J</sub> = 125 °C		-	85	-	A∕µs

THERMAL - MECHANICAL SPECIFICATIONS							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Lead temperature	T <sub>lead</sub>	0.063" from case (1.6 mm) for 10 s	-	-	300	°C	
Thermal resistance, junction to case	R <sub>thJC</sub>		-	-	1.7		
Thermal resistance, junction to ambient	R <sub>thJA</sub>	Typical socket mount	-	-	40	K/W	
Thermal resistance, case to heatsink	R <sub>thCS</sub>	Mounting surface, flat, smooth and greased	-	0.25	-		
Weight			-	6.0	-	g	
weight			-	0.21	-	oz.	
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)	
Marking device		Case style TO-247AC 2L	HFA08PB120				

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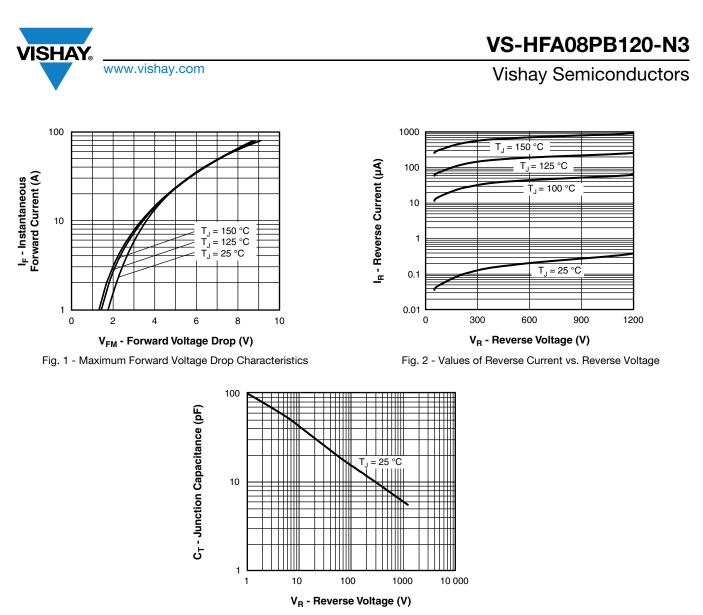


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

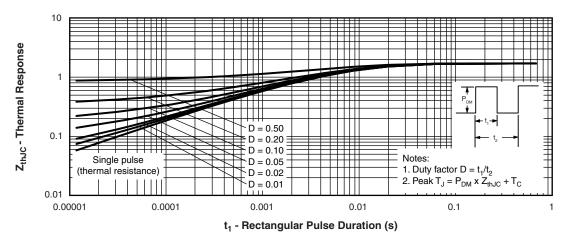
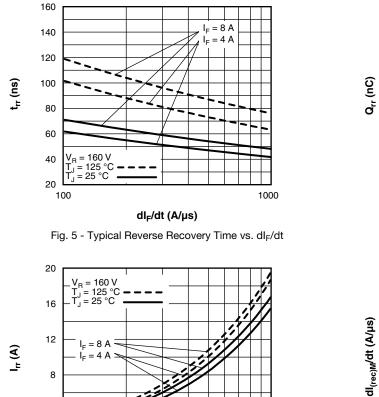
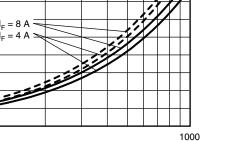


Fig. 4 - Maximum Thermal Impedance ZthJC Characteristics



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dl<sub>F</sub>/dt (A/µs)

8

4

0

100

Fig. 6 - Typical Recovery Current vs. dl<sub>F</sub>/dt

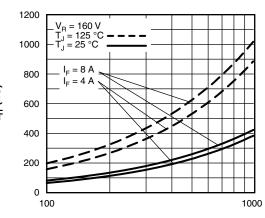




Fig. 7 - Typical Stored Charge vs. dl<sub>F</sub>/dt

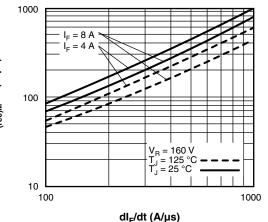


Fig. 8 - Typical  $dI_{(rec)M}/dt$  vs.  $dI_F/dt$ 

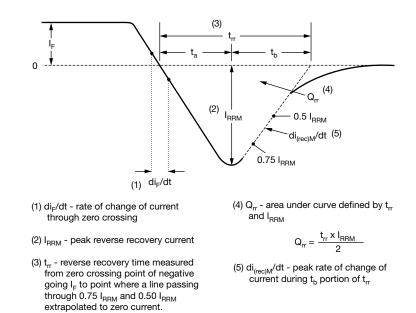


Fig. 9 - Reverse Recovery Waveform and Definitions

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#### **ORDERING INFORMATION TABLE**

Device code	VS-	HF	Α	08	РВ	120	-N3
	1	2	3	4	5	6	7
	1 · 2 · 3 · 4 ·	HE Elec Cur	XFRED <sup>®</sup> ctron irra		- 8A)	oduct	
	6 - 7 -	Env	ironmer	ng: (120 ntal digit en-free,	:	,	int, and

ORDERING INFORMATION (Example)						
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION			
VS-HFA08Pb120-N3	25	500	Antistatic plastic tube			

LINKS TO RELATED DOCUMENTS				
Dimensions www.vishay.com/doc?96144				
Part marking information www.vishay.com/doc?95648				



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